

BCM857BV

E2

45V MATCHED PAIR PNP SMALL SIGNAL TRANSISTOR IN SOT563

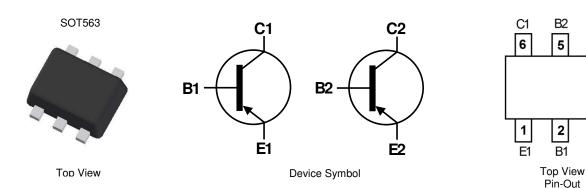
Features

- BV_{CEO} > -45V
- I_C = -100mA High Collector Current
- Pair of PNP Transistors That Are Intrinsically Matched (Note 1)
- 2% Matching on Current Gain (h_{FE})
- 2mV Matching on Base-Emitter Voltage (V_{BE})
- Fully Internally Isolated in a Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 2 & 3)
- Halogen and Antimony Free. "Green" Device (Note 4)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: SOT563
- Package Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208@3
- Weight: 0.003 grams (Approximate)



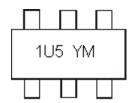
Ordering Information (Note 5)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
BCM857BV-7	1U5	7	8	3,000

Notes:

- 1. Intrinsically matched pair as this is built with adjacent die from the same wafer.
- 2. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 3. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 4. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



1U5 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: J = 2022) M = Month (ex: 9 = September)

Date Code Key

Year	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Code	J	K	L	М	N	0	Р	R	S	T	U	V
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-50	V
Collector-Emitter Voltage	V _{CEO}	-45	V
Emitter-Base Voltage	V _{EBO}	-5.0	V
Collector Current	Ic	-100	mA
Peak Collector Current	I _{CM}	-200	mA
Peak Base Current	I _{BM}	-200	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation. Total Device (Note 6)	P_{D}	500	mW
Power Dissipation. Single Transistor (Note 7)	P_{D}	357	mW
Thermal Resistance, Junction to Ambient Air (Note 6)	$R_{\theta JA}$	+250	°C/W
Thermal Resistance, Junction to Ambient Air (Note 7)	R _{0JA}	+350	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-65 to +150	°C

ESD Ratings (Note 8)

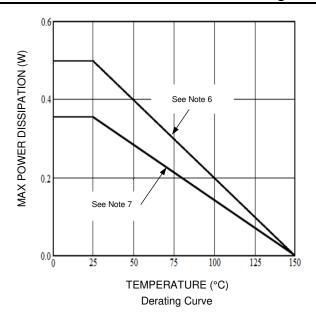
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	٧	С

Notes:

- 6. For a device with two active die running at equal power, mounted on minimum recommended pad layout with 1oz copper that is on a single-sided 1.6mm FR4 PCB; the device is measured under still air conditions whilst operating in a steady-state.
 7. Same as Note 6 except for only one active die running.
 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic (Note 9)	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-50	_	_	V	$I_C = -100 \mu A, I_B = 0$
Collector-Emitter Breakdown Voltage	BV _{CEO}	-45	_	_	V	$I_C = -10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV _{EBO}	-5	_	_	V	$I_E = -100 \mu A$, $I_C = 0$
DC Current Gain	h _{FE}	200	290	450	_	$V_{CE} = -5.0V, I_{C} = -2.0mA$
DC Current Gain Matching (Note 10)	h _{FE1} /h _{FE2}	0.98	1	_	_	$V_{CE} = -5.0V$, $I_{C} = -2.0mA$
Collector-Emitter Saturation Voltage	V _{CE(sat)}	_	-50 -200	-200 -400	mV	$I_C = -10$ mA, $I_B = -0.5$ mA $I_C = -100$ mA, $I_B = -5.0$ mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	_	-760	_	mV	$I_C = -10mA$, $I_B = -0.5mA$
Base-Emitter Voltage	V _{BE(on)}	-600	-650	-700	mV	$V_{CE} = -5.0V, I_{C} = -2.0mA$
Base-Emitter Voltage Matching (Note 11)	V _{BE1(on)} - V _{BE2(on)}	_	_	2	mV	$V_{CE} = -5.0V, I_{C} = -2.0mA$
Collector Cut-Off Current	I _{CBO}	_	_	-15 -5.0	nA μA	V _{CB} = -30V V _{CB} = -30V, T _A = +150°C
Emitter Cut-Off Current	I _{EBO}	_	_	-100	nA	$V_{EB} = -5.0V, I_{C} = 0$
Gain Bandwidth Product	f _T	100	175	_	MHz	$V_{CE} = -5.0V, I_{C} = -10mA,$ f = 100MHz
Collector-Base Capacitance	Ссво		_	2.2	pF	V _{CB} = -10V, f = 1.0MHz
Emitter-Base Capacitance	C _{EBO}		10	_	pF	V _{EB} = -0.5V, f = 1.0MHz

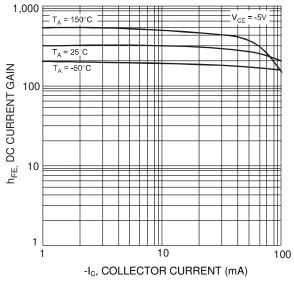
^{9.} Short duration pulse test used to minimize self-heating effect.

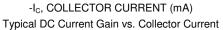
^{10.} The smaller of the two values is taken as the numerator.

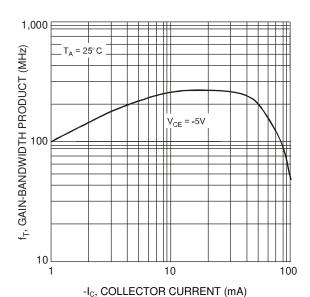
11. The smaller of the two values is subtracted from the larger value.



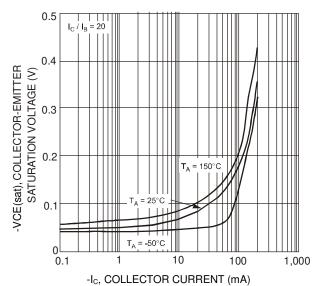
Typical Electrical Characteristics (@TA = +25°C unless otherwise specified.)







Typical Gain-Bandwidth Product vs. Collector Current



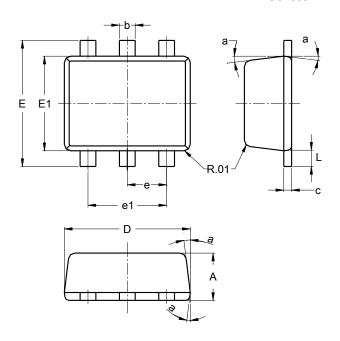
Typical Collector-Emitter Saturation Voltage vs. Collector Current



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT563

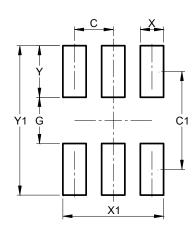


SOT563					
Dim	Min	Max	Тур		
Α	0.55	0.60			
b	0.15	0.30	0.20		
С	0.10	0.18	0.11		
D	1.50	1.70	1.60		
Е	1.55	1.70	1.60		
E1	1.10	1.25	1.20		
е			0.50		
e1	0.90	1.10	1.00		
L	0.10	0.30	0.20		
а	8°	9°	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT563



Dimensions	Value (in mm)
С	0.500
C1	1.270
G	0.600
Х	0.300
X1	1.300
Υ	0.670
Y1	1.940



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